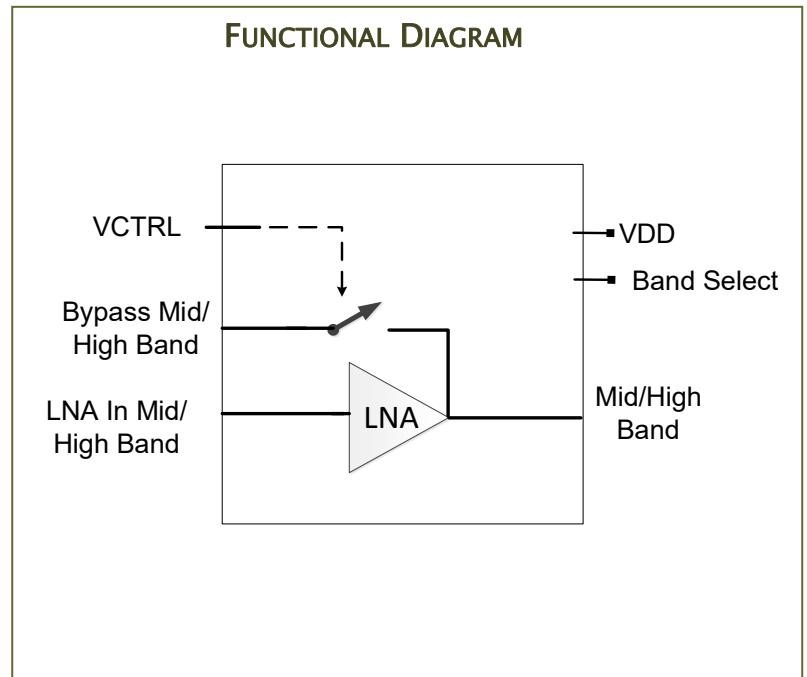


### Features

- ☑ CMOS SOI LNA for Mid/High Band cellular applications.
- ☑ High Power Bypass path can handle up to 36dBm which allows it to function both in RX mode and TX mode (for TDD applications)
- ☑ Band of operation selectable as either Mid Band or High Band
- ☑ ESD protection on all ports .
- ☑ Noise Figure < 1dB
- ☑ Gain > 15dB
- ☑ Single supply with 2.3V to 4.8V operating range.



### Description

The FE213602 is a CMOS SOI LNA for cellular applications. It integrates a Mid/High Band LNA and a high power bypass path.

In active mode the LNA provides greater than 15dB gain and less than 1dB Noise Figure. The bypass path has less than 1dB loss and can be used in Rx mode or TX mode with power levels up to 36dBm. The band of operation is selectable for either Mid Band Or High Band operation, so the same component can be used for both bands.

The LNA runs from a single supply with an operating range from 2.3V up to 4.8V. External DC blocking capacitors are not required on the RF ports unless there is a DC voltage

externally applied to the ports.

The device is fabricated using a high performance CMOS SOI process optimized for RF front-end applications.

The FE213602 integrates ESD protection on all ports but also integrates ESD protection between the RF ports and the VDD and control ports to support high reliability manufacturing.

The die will be available in die form for flip-chip assembly and will be RoHS compliant to EU Directive 2002/95/EC.

## Further Information

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Please contact [sales@ferfics.com](mailto:sales@ferfics.com)